## **3.3V Differential LVPECL/LVDS/CML to LVTTL/LVCMOS Translator**

The MC100EPT21 is a Differential LVPECL/LVDS/CML to LVTTL/LVCMOS translator. Because LVPECL (Positive ECL), LVDS, and positive CML input levels and LVTTL/LVCMOS output levels are used, only +3.3 V and ground are required. The small outline 8–lead SOIC package makes the EPT21 ideal for applications which require the translation of a clock or data signal.

The V<sub>BB</sub> output allows this EPT21 to be cap coupled in either single–ended or differential input mode. When single–ended cap coupled, V<sub>BB</sub> output is tied to the  $\overline{D}$  input and D is driven for a non–inverting buffer, or V<sub>BB</sub> output is tied to the D input and  $\overline{D}$  is driven for an inverting buffer. When cap coupled differentially, V<sub>BB</sub> output is connected through a resistor to each input pin. If used, the V<sub>BB</sub> pin should be bypassed to V<sub>CC</sub> via a 0.01 µF capacitor. For additional information see AND8020/D. For a single–ended direct connection use an external voltage reference source such as a resistor divider. Do not use V<sub>BB</sub> for a single–ended direct connection or port to another device.

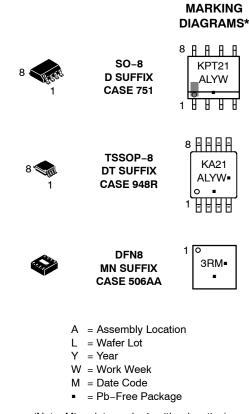
### Features

- 1.4 ns Typical Propagation Delay
- Maximum Frequency > 275 MHz Typical
- LVPECL/LVDS/CML Inputs, LVTTL/LVCMOS Outputs
- 24 mA TTL outputs
- Operating Range:  $V_{CC} = 3.0 \text{ V}$  to 3.6 V with GND = 0 V
- The 100 Series Contains Temperature Compensation
- V<sub>BB</sub> Output
- These Devices are Pb-Free and are RoHS Compliant



### **ON Semiconductor®**

http://onsemi.com

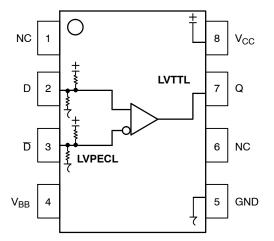


(Note: Microdot may be in either location)

\*For additional marking information, refer to Application Note AND8002/D.

### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.



### Figure 1. Logic Diagram and 8-Lead Pinout (Top View)

### Table 1. PIN DESCRIPTION

PIN	FUNCTION
Q	LVTTL/LVCMOS Output
D*, <u>D</u> *	Differential LVPECL/LVDS/CML Input
V <sub>CC</sub>	Positive Supply
V <sub>BB</sub>	Output Reference Voltage
GND	Ground
NC	No Connect
EP	(DFN8 only) Thermal exposed pad must be connected to a sufficient thermal conduit. Elec- trically connect to the most negative supply (GND) or leave unconnected, floating open.

Pin will default to 1/2 of V<sub>CC</sub> when left open.

Character	istics	Value
Internal Input Pulldown Resistor	D	50 k $\Omega$
Internal Input Pulldown Resistor	D	50 k $\Omega$
Internal Input Pullup Resistor	D, D	50 kΩ
ESD Protection	Human Body Model Machine Model Charged Device Model	> 1.5 kV > 100 V > 2 kV
Moisture Sensitivity, Indefinite Time	e Out of Drypack (Note 1) SOIC-8 TSSOP-8 DFN8	Level 1 Level 3 Level 1
Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in
Transistor Count		81 Devices

\*

1. For additional information, see Application Note AND8003/D.

### **Table 3. MAXIMUM RATINGS**

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V <sub>CC</sub>	PECL Power Supply	GND = 0 V		3.8	V
V <sub>IN</sub>	PECL Input Voltage	GND = 0 V	$V_{I}\!\leq\!V_{CC}$	0 to 3.8	V
I <sub>BB</sub>	V <sub>BB</sub> Sink/Source			± 0.5	mA
T <sub>A</sub>	Operating Temperature Range			-40 to +85	°C
T <sub>stg</sub>	Storage Temperature Range			-65 to +150	°C
$\theta_{JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SO-8 SO-8	190 130	°C/W °C/W
$\theta_{\text{JC}}$	Thermal Resistance (Junction-to-Case)	Standard Board	SO-8	41 to 44	°C/W
$\theta_{JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP-8 TSSOP-8	185 140	°C/W °C/W
$\theta_{\text{JC}}$	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44	°C/W
$\theta_{JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	DFN8 DFN8	129 84	°C/W °C/W
T <sub>sol</sub>	Wave Solder Pb Pb-Free	< 2 to 3 sec @ 248°C <2 to 3 sec @ 260°C		265 265	°C
$\theta_{\text{JC}}$	Thermal Resistance (Junction-to-Case)	(Note 2)	DFN8	35 to 40	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

2. JEDEC standard multilayer board - 2S2P (2 signal, 2 power)

### Table 4. PECL INPUT DC CHARACTERISTICS V<sub>CC</sub> = 3.3 V, GND = 0.0 V (Note 3)

		-40°C		25°C			85°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
VIH	Input HIGH Voltage (Single-Ended)	2075		2420	2075		2420	2075		2420	mV
VIL	Input LOW Voltage (Single-Ended)	1355		1675	1355		1675	1355		1675	mV
V <sub>BB</sub>	Output Voltage Reference	1775	1875	1975	1775	1875	1975	1775	1875	1975	mV
V <sub>IHCMR</sub>	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 4)	1.2		3.3	1.2		3.3	1.2		3.3	V
I <sub>IH</sub>	Input HIGH Current			150			150			150	μA
IIL	Input LOW Current	-150			-150			-150			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

Input parameters vary 1:1 with V<sub>CC</sub>.
V<sub>IHCMR</sub> min varies 1:1 with GND, V<sub>IHCMR</sub> max varies 1:1 with V<sub>CC</sub>. The V<sub>IHCMR</sub> range is referenced to the most positive side of the differential input signal.

Symbol	Characteristic	Condition	Min	Tun	Max	Unit
Symbol	Characteristic	Condition	IVIIII	Тур	INIAX	Unit
V <sub>OH</sub>	Output HIGH Voltage	I <sub>OH</sub> = -3.0 mA	2.4			V
V <sub>OL</sub>	Output LOW Voltage	I <sub>OL</sub> = 24 mA			0.5	V
I <sub>CCH</sub>	Power Supply Current	Outputs set to HIGH	5	17	25	mA
I <sub>CCL</sub>	Power Supply Current	Outputs set to LOW	8	21	30	mA
los	Output Short Circuit Current		-130		-80	mA

### Table 5. LVTTL/LVCMOS OUTPUT DC CHARACTERISTICS $V_{CC} = 3.3 \text{ V}$ , GND = 0.0 V, $T_A = -40^{\circ}\text{C}$ to $85^{\circ}\text{C}$

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

			-40°C		25°C			85°C				
Symbol	Characteristic		Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f <sub>max</sub>	Maximum Frequency (Figure 2)		275	350		275	350		275	350		MHz
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay to Output Differential		800 1200	1400 1400	2050 1800	800 1200	1400 1400	2250 1800	900 1100	1600 1300	2950 1900	ps
t <sub>SKEW</sub>	Duty Cycle Skew (Note 6)		45	50	55	45	50	55	45	50	55	%
t <sub>SKPP</sub>	Part-to-Part Skew (Note 6)				500			500			500	ps
t <sub>JITTER</sub>	Random Clock Jitter (RMS)			3.5	5		3.5	5		3.5	5	ps
V <sub>PP</sub>	Input Voltage Swing (Differential Configuration)		150	800	1200	150	800	1200	150	800	1200	mV
t <sub>r</sub> t <sub>f</sub>	Output Rise/Fall Times (0.8V – 2.0V)	Q, <u>Q</u>	250	600	900	250	600	900	250	600	900	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

5. Measured with a 750 mV 50% duty-cycle clock source.  $R_L = 500 \Omega$  to GND and  $C_L = 20 \text{ pF}$  to GND. Refer to Figure 3.

6. Skews are measured between outputs under identical transitions. Duty cycle skew is measured between differential outputs using the deviations of the sum Tpw- and Tpw+.

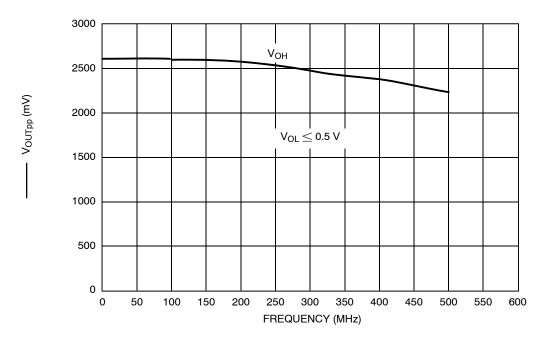


Figure 2. F<sub>max</sub>

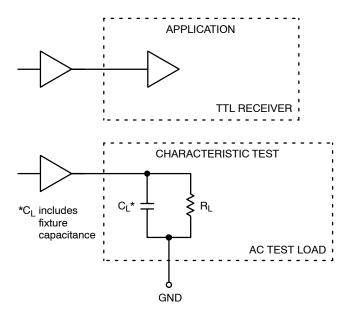


Figure 3. TTL Output Loading Used For Device Evaluation

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC100EPT21DG	SOIC-8 (Pb-Free)	98 Units / Rail
MC100EPT21DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC100EPT21DTG	TSSOP-8 (Pb-Free)	100 Units / Rail
MC100EPT21DTR2G	TSSOP-8 (Pb-Free)	2500 / Tape & Reel
MC100EPT21MNR4G	DFN8 (Pb-Free)	1000 / Tape & Reel

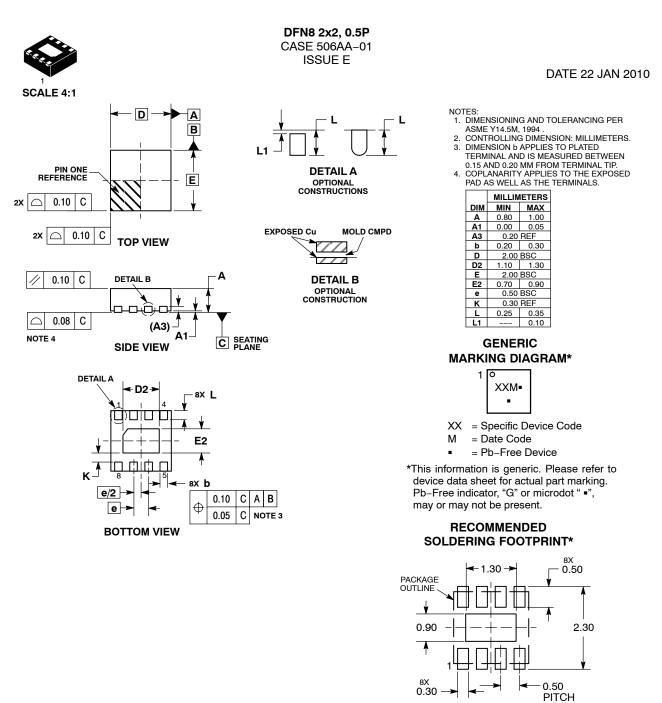
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### **Resource Reference of Application Notes**

AN1405/D	-	ECL Clock Distribution Techniques
AN1406/D	-	Designing with PECL (ECL at +5.0 V)
AN1503/D	-	ECLinPS <sup>™</sup> I/O SPiCE Modeling Kit
AN1504/D	_	Metastability and the ECLinPS Family
AN1568/D	-	Interfacing Between LVDS and ECL
AN1672/D	_	The ECL Translator Guide
AND8001/D	-	Odd Number Counters Design
AND8002/D	-	Marking and Date Codes
AND8020/D	-	Termination of ECL Logic Devices
AND8066/D	-	Interfacing with ECLinPS
AND8090/D	_	AC Characteristics of ECL Devices

ECLinPS is a trademark of Semiconductor Components Industries, LLC (SCILLC).



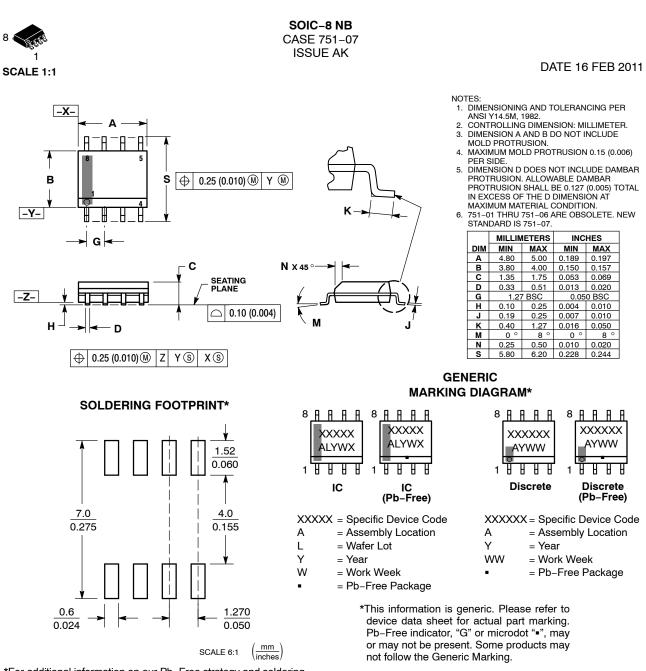


DIMENSIONS: MILLIMETERS

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON18658D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.							
DESCRIPTION:	DFN8, 2.0X2.0, 0.5MM PITCH PAGE 1 OI								
ON Semiconductor reserves the right the suitability of its products for any pa	to make changes without further notice to an articular purpose, nor does ON Semiconducto	ON Semiconductor and (iii) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the							





\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.					
DESCRIPTION:	SOIC-8 NB	PAGE 1 OF 2					
the suitability of its products for any pa	articular purpose, nor does ON Semiconducto	stries, LLC dba ON Semiconductor or its subsidiaries in the United States y products herein. ON Semiconductor makes no warranty, representation r assume any liability arising out of the application or use of any product or icidental damages. ON Semiconductor does not convey any license under	r circuit, and specifically				

© Semiconductor Components Industries, LLC, 2019

#### SOIC-8 NB CASE 751-07 **ISSUE AK**

STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER EMITTER 5. BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6. BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5.

6.

7.

8 GATE 1

SOURCE 1/DRAIN 2

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. 4. DRAIN, #2 GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. З. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. LINE 1 OUT 8. STYLE 27: PIN 1. ILIMIT OVI O 2 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

#### DATE 16 FEB 2011

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW\_TO\_GND 2. DASIC OFF DASIC\_SW\_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

DOCUMENT NUMBER:	98ASB42564B	<b>8ASB42564B</b> Electronic versions are uncontrolled except when accessed directly from the Document Reposition Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.				
DESCRIPTION:	SOIC-8 NB	PAGE 2 OF 2				
ON Semiconductor reserves the right the suitability of its products for any pa	to make changes without further notice to an inticular purpose, nor does ON Semiconducto	stries, LLC dba ON Semiconductor or its subsidiaries in the United States y products herein. ON Semiconductor makes no warranty, representation r assume any liability arising out of the application or use of any product or icidental damages. ON Semiconductor does not convey any license under	or guarantee regarding r circuit, and specifically			

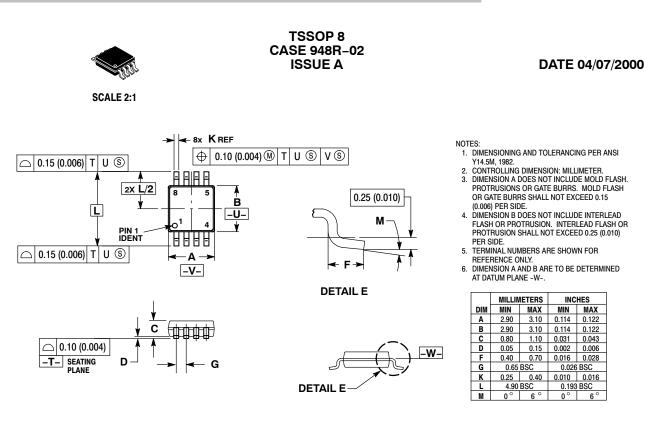
7.

8

COLLECTOR, #1

COLLECTOR, #1





DOCUMENT NUMBER:	98AON00236D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TSSOP 8		PAGE 1 OF 1
ON Semiconductor and where a trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.			

© Semiconductor Components Industries, LLC, 2019

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and calcular performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

#### TECHNICAL SUPPORT

onsemi Website: www.onsemi.com

Email Requests to: orderlit@onsemi.com

North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative

٥